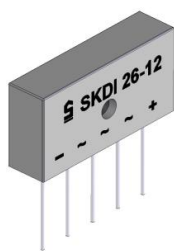


SKDI 26



3~phase

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SKDI 26

Preliminary Data

Features

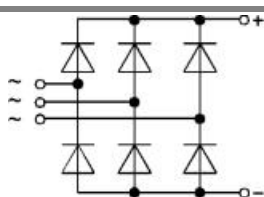
- In-line isolated metal case with wired connectors
- Heat sink mounting not on the marking side
- Blocking voltage to 1600V
- High surge current
- Easy mounting
- UL recognized, file no. E 63 532

Typical Applications

- Three phase rectifier for power supplies
- Input rectifier for variable frequency drives
- Rectifier for DC motor field supplies
- Battery charger
- Recommended snubber network:
RC: 50Ω, 0,1μF

V_{RSM}, V_{RRM} V	V_{VRMS} V	$I_D = 20 \text{ A } (T_A = 50 \text{ }^\circ\text{C})$ Types	C_{max} μF	R_{min} Ω
200	60	SKDI 26/02	25000	0,15
400	125	SKDI 26/04	12200	0,3
600	185	SKDI 26/06	8300	0,5
800	250	SKDI 26/08	6100	0,7
1000	310	SKDI 26/10	5000	0,85
1200	380	SKDI 26/12	4000	1
1400	440	SKDI 26/14	3500	1,2
1600	500	SKDI 26/16	3000	1,5

Symbol	Conditions	Values	Units
I_D	$T_a = 50 \text{ }^\circ\text{C}$, isolated	4	A
	$T_a = 50 \text{ }^\circ\text{C}$, P1A/120	20	A
I_{DCL}	$T_a = 50 \text{ }^\circ\text{C}$, isolated	4	A
	$T_a = 50 \text{ }^\circ\text{C}$, P1A/120	20	A
	$T_a = \text{ }^\circ\text{C}$,		A
I_{FSM}	$T_{vj} = 25 \text{ }^\circ\text{C}$, 10 ms	370	A
	$T_{vj} = 150 \text{ }^\circ\text{C}$, 10 ms	320	A
i^2t	$T_{vj} = 25 \text{ }^\circ\text{C}$, 8,3 ... 10 ms	680	A ² s
	$T_{vj} = 150 \text{ }^\circ\text{C}$, 8,3 ... 10 ms	500	A ² s
V_F	$T_{vj} = 25 \text{ }^\circ\text{C}$, $I_F = 12,5 \text{ A}$	max. 1,1	V
$V_{(TO)}$	$T_{vj} = 150 \text{ }^\circ\text{C}$	max. 0,85	V
r_T	$T_{vj} = 150 \text{ }^\circ\text{C}$	max. 12	mΩ
I_{RD}	$T_{vj} = 25 \text{ }^\circ\text{C}$, $V_{RD} = V_{RRM} = 1600 \text{ V}$	300	μA
	$T_{vj} = \text{ }^\circ\text{C}$, $V_{RD} = V_{RRM} \geq V$		μA
I_{RD}	$T_{vj} = 150 \text{ }^\circ\text{C}$, $V_{RD} = V_{RRM} = 1600 \text{ V}$	5	mA
	$T_{vj} = \text{ }^\circ\text{C}$, $V_{RD} = V_{RRM} \geq V$		mA
t_{rr}	$T_{vj} = 25 \text{ }^\circ\text{C}$	10	μs
f_G		2000	Hz
$R_{th(j-a)}$	isolated	8	K/W
	chassis	5,1	K/W
$R_{th(j-c)}$	total	4,1	K/W
$R_{th(c-s)}$	total	0,15	K/W
T_{vj}		-50...+150	°C
T_{stg}		-50...+150	°C
V_{isol}	a.c. 50..60Hz; r.m.s.; 1s/1min	3000/2500	V~
M_s	to heatsink	2±10%	Nm
M_t			Nm
a			m/s ²
w		35	g
F_u		40	A
Case			



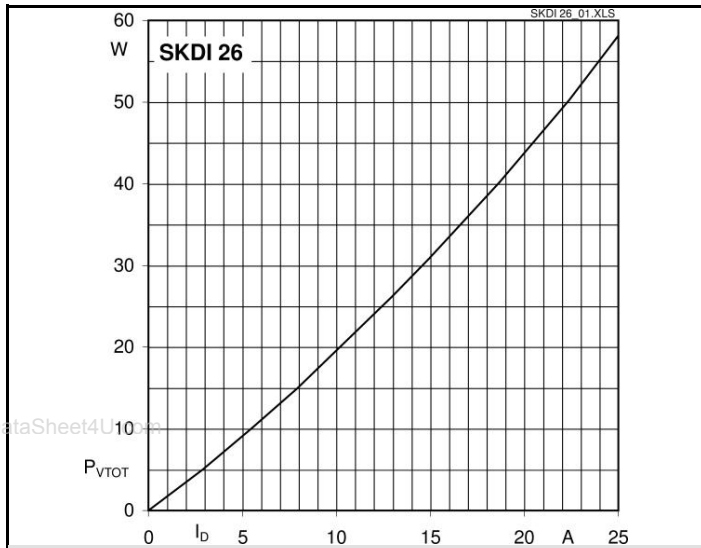


Fig. 3L Power dissipation vs. output current

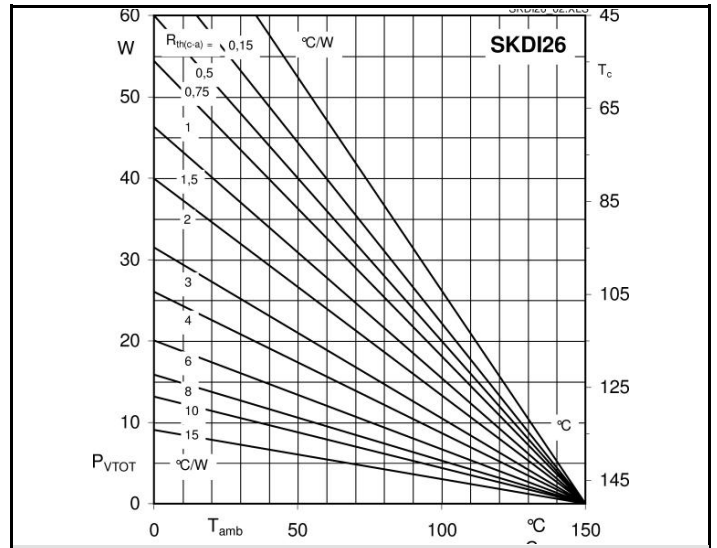


Fig. 3R Power dissipation vs. case temperature

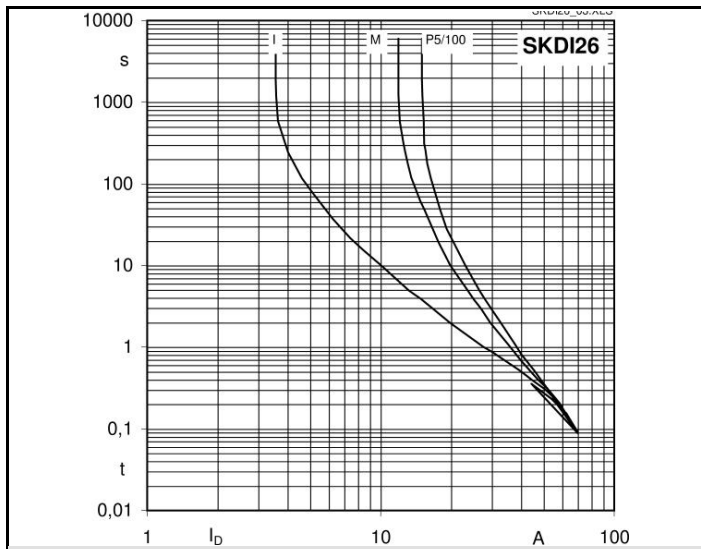


Fig. 6 Rated overload characteristics vs. time

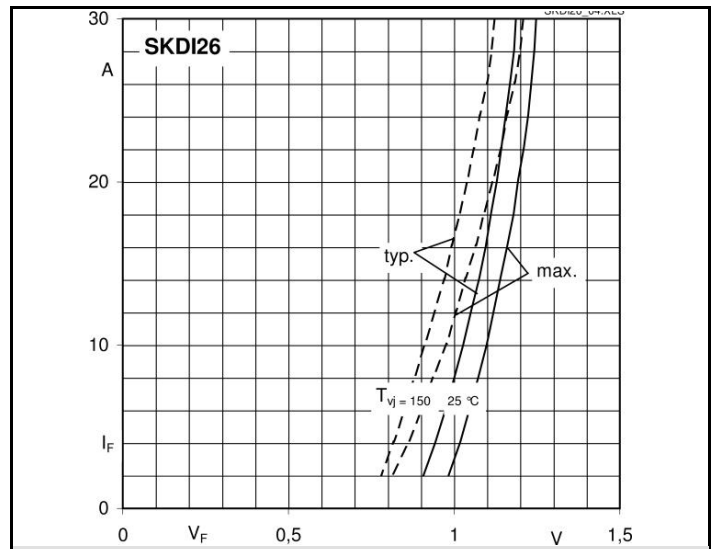
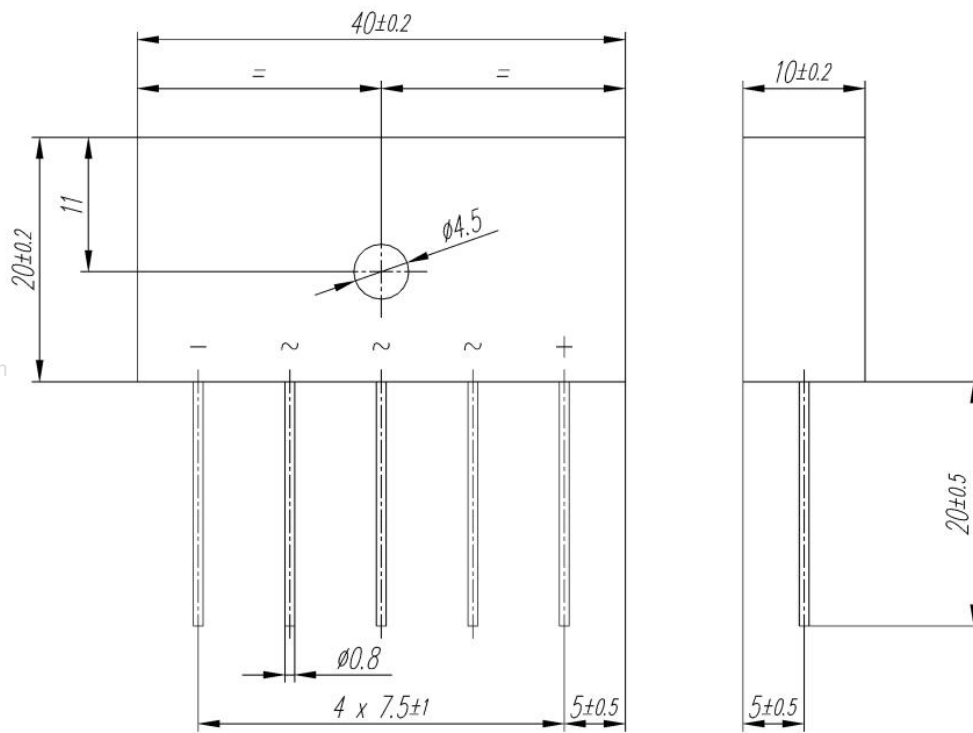


Fig. 9 Forward characteristics of a diode arm



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